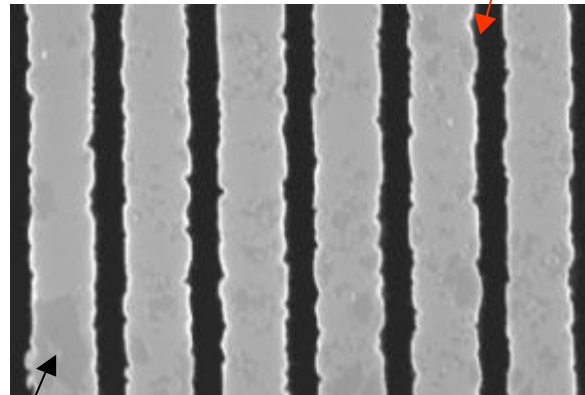


Etching solution

Striation or Line Edge Roughing

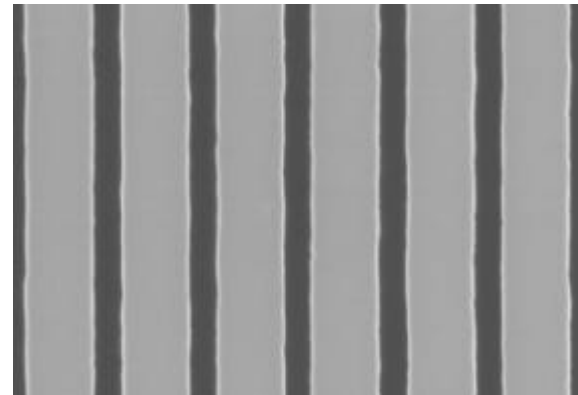


Dielectrics

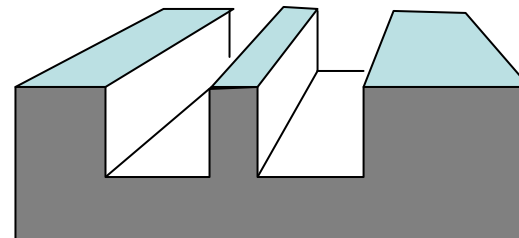
Trench etched by an old technology



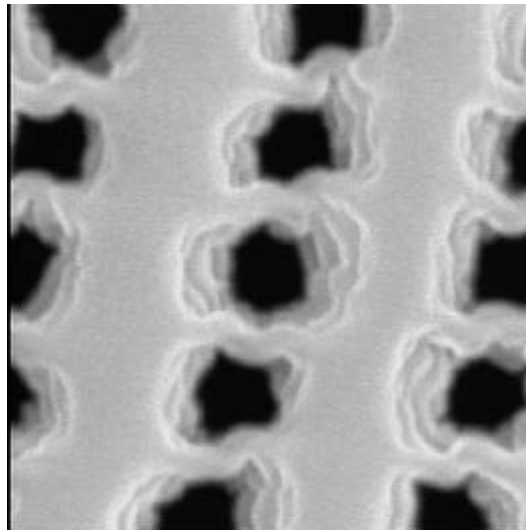
Striation-free SiO₂ etch



100nm

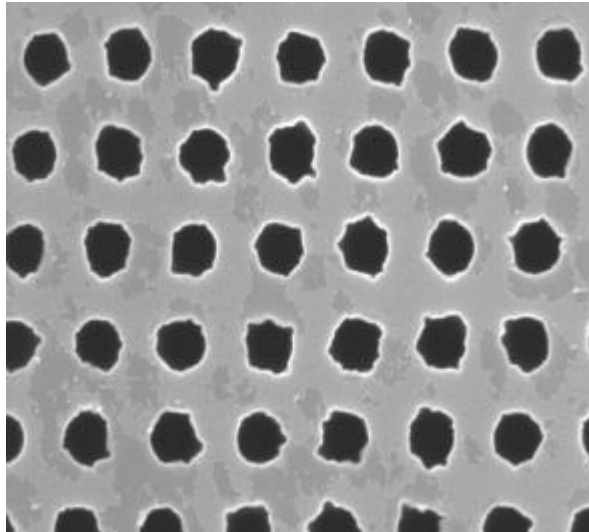


Striation or line edge roughness (LER)
of resist pattern after plasma exposure



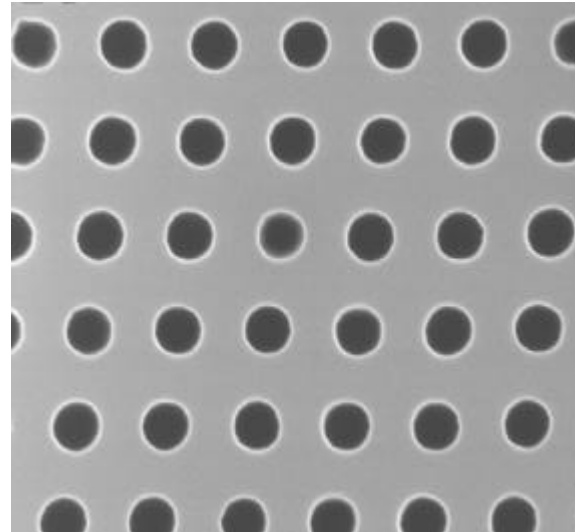
Striation results by using a Philwafer

traditional



Big problem

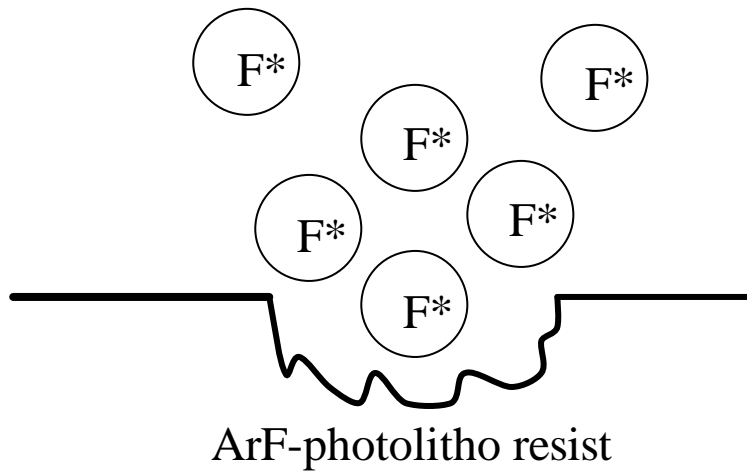
Philtech solution



Good Yield

Discussion

Plasma dissociate C_xF_y compounds to form F^* , CF , CF_2 , CF_3 species



C_3F_7I emits I

I easily reacts with F^* to form inert IF_3 , IF_5 , IF_7 effectively

